

DTS5606

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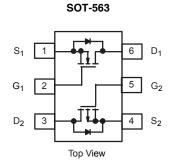
N- and P-Channel 20 V (D-S) MOSFET

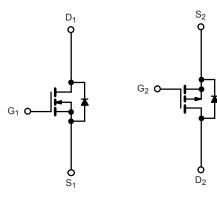
PRODUCT SUMMARY						
	V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)			
N-Channel	20	0.299 at V _{GS} = 4.5 V	1.2			
		0.426 at V _{GS} = 2.5 V	0.9			
P-Channel	- 20	0.689 at V _{GS} = - 4.5 V	- 0.5			
		0.873 at V _{GS} = - 2.5 V	- 0.4			

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC







N-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATIN	GS T _A = 25 °	°C, unless other	wise noted			
Parameter		Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage		V _{DS}	20	- 20	V	
Gate-Source Voltage		V _{GS}	12	-12		
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 25 °C	- I _D	1.2	- 0.5		
	T _A = 70 °C		0.9	- 0.4	•	
Pulsed Drain Current		I _{DM}	3.5	- 2	A	
n	T _A = 25 °C	P _D	1.15		W	
Maximum Power Dissipation ^{a, b}	T _A = 70 °C	- FD	0.			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
THERMAL RESISTANCE RATI	NGS					
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	$t \le 10 s$	R _{thJA}	130	200	°C/W	
Maximum Junction-to-Lead	Steady State	R _{thJL}	85	190	C/ W	

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static		•						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	N-Ch	0.4		1.2	v	
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 0.4		- 1.2		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V	N-Ch			± 100	nA	
			P-Ch			± 100		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 16 V, V_{GS} = 0 V	N-Ch			1	μΑ	
		V _{DS} = - 16 V, V _{GS} = 0 V	P-Ch			- 1		
		V_{DS} = 16V, V_{GS} = 0 V, T_{J} = 55 °C	N-Ch			10		
		V _{DS} = - 16V, V _{GS} = 0 V, T _J = 55 °C	P-Ch			- 5		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	N-Ch	3.5			A	
		V _{DS} = - 5 V, V _{GS} = - 10 V	P-Ch	- 2				
Drain-Source On-State Resistance ^a		V _{GS} = 4.5 V, I _D = 0.8 A	N-Ch		0.299	0.331	Ω	
	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -0.4 \text{ A}$	P-Ch		0.689	0.760		
		$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 0.5 \text{ A}$	N-Ch		0.426	0.470		
		$V_{GS} = -2.5 \text{ V}, \text{ I}_{D} = -0.2 \text{ A}$	P-Ch		0.420	0.997		
Forward Transconductance ^a	9 _{fs}	$V_{\rm DS} = 10 \text{ V}, \text{ I}_{\rm D} = 0.8 \text{ A}$	N-Ch		3.1	0.337	- S	
		V _{DS} = - 15 V, I _D = - 0.5 A	P-Ch		2.8			
Diode Forward Voltage ^a	V _{SD}	$I_{\rm S} = 0.8 \text{ A}, V_{\rm GS} = 0 \text{ V}$	N-Ch		0.8	1.10	- V	
		$I_{\rm S} = -0.6 \text{ A}, V_{\rm GS} = 0 \text{ V}$	P-Ch		- 0.75	- 1.2		
Dynamic ^b			1 011		- 0.13	- 1.2	I	
Dynamic			N-Ch		1.6	2.2		
Total Gate Charge	Qg	N-Channel	P-Ch		2.1	2.6	nC	
		V_{DS} = 10 V, V_{GS} = 4.5 V, I_{D} = 0.5 A	N-Ch		0.1	2.0		
Gate-Source Charge	Q _{gs}	D. Channel	P-Ch		0.4			
Gate-Drain Charge	Q _{gd}	P-Channel V _{DS} = - 10 V, V _{GS} = - 4.5 V,	N-Ch		0.2			
		$I_{\rm D} = -0.3 \rm{A}$	P-Ch		0.5			
Gate Resistance	R _g		N-Ch	2.5		3.9	Ω	
			P-Ch	3		4.5		
Turn-On Delay Time Rise Time Turn-Off Delay Time	t _{d(on)} t _r	N-Channel V_{DD} = 15 V, R _L = 15 Ω	N-Ch		9			
			P-Ch		8		ns	
		$I_D \cong 0.5 \text{ A}, V_{GEN} = 10 \text{ V}, \text{ R}_g = 6 \Omega$	N-Ch		19			
		4	P-Ch		5.6			
		P-Channel $V_{1} = 15 V_{1} R_{2} = 15 O_{2}$	N-Ch P-Ch		23 12			
Fall Time	t _f	$V_{DD} = -15 \text{ V}, \text{R}_{\text{L}} = 15 \Omega \qquad \text{P-Ch}$ $\text{I}_{D} \cong -0.5 \text{ A}, \text{V}_{\text{GEN}} = -10 \text{ V}, \text{R}_{\text{g}} = 6 \Omega \qquad \text{N-Ch}$			7		-	
		$M_{\rm D} = 0.0$ A, $V_{\rm GEN} = 10$ V, $M_{\rm g} = 0.22$	P-Ch		6.9		†	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 0.6 A, dl/dt = 100 A/μs	N-Ch		6.3		-	
		$I_{\rm F} = -0.6 \text{ A}, \text{ dl/dt} = 100 \text{ A/}\mu\text{s}$	11 011		0.0			

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

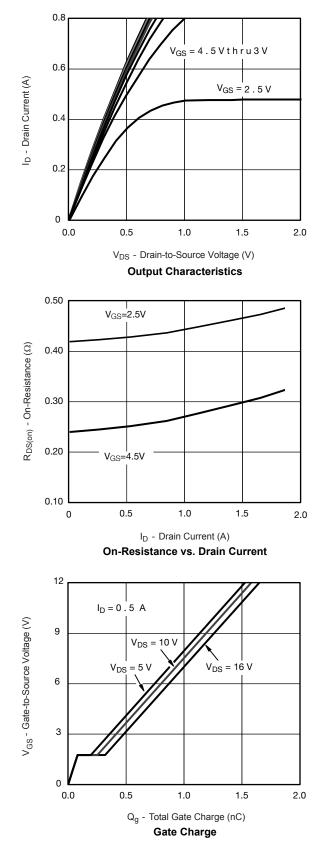
b. Guaranteed by design, not subject to production testing.

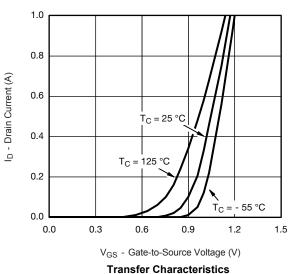
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

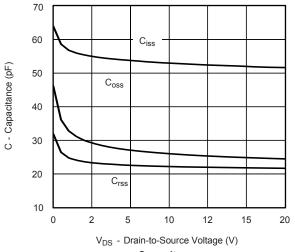
Din-Tek SEMICONDUCTOR

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

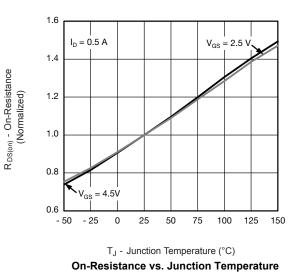








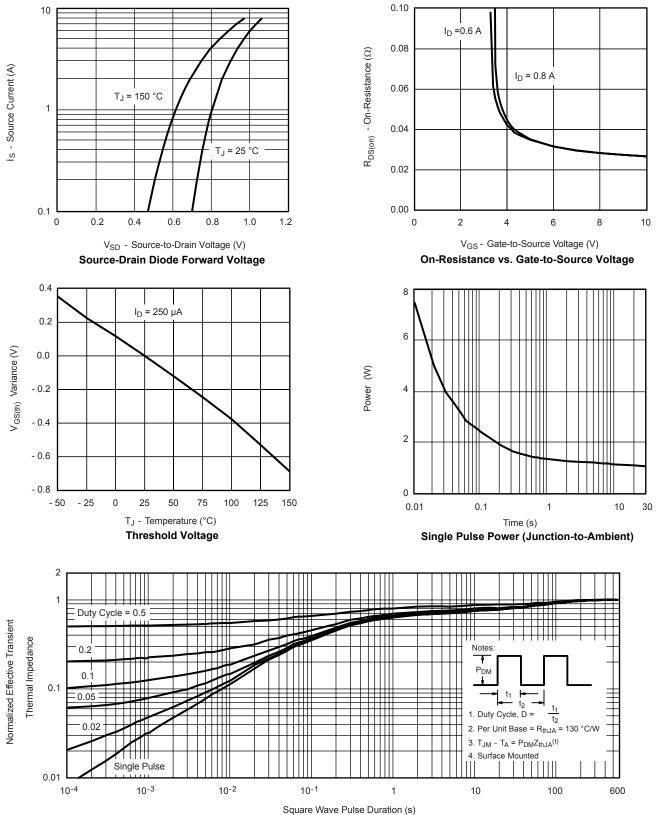




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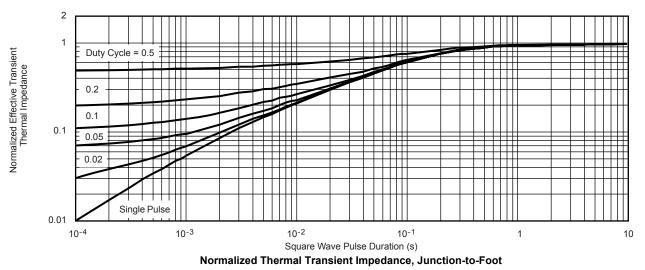


N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

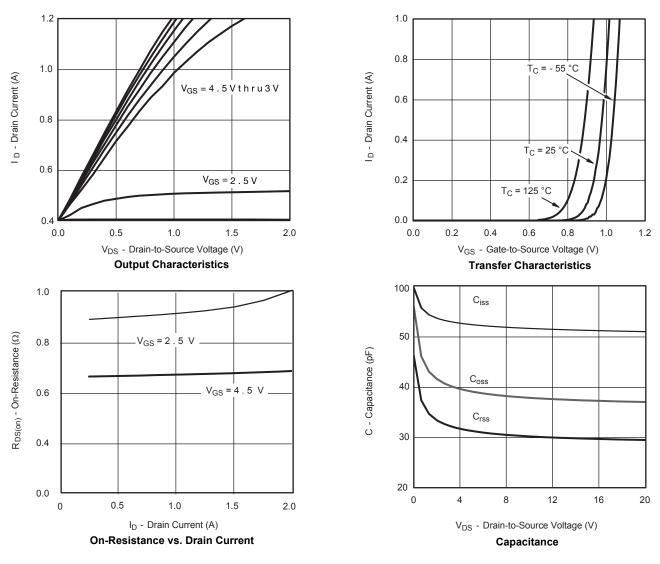


Normalized Thermal Transient Impedance, Junction-to-Ambient



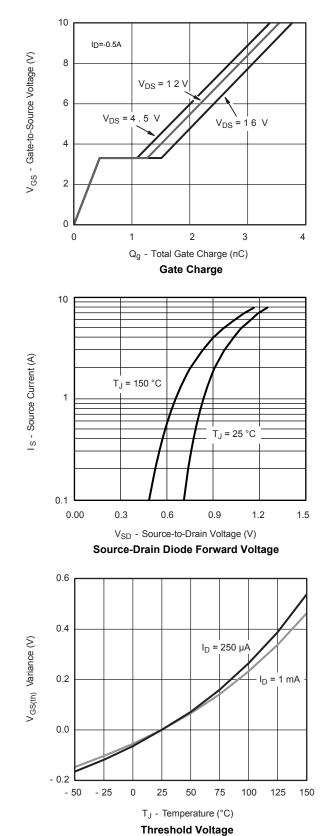


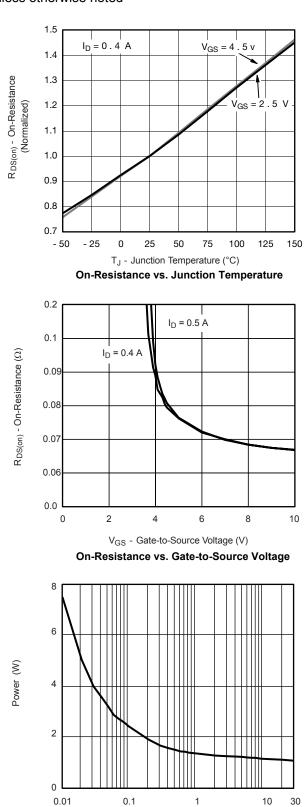
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





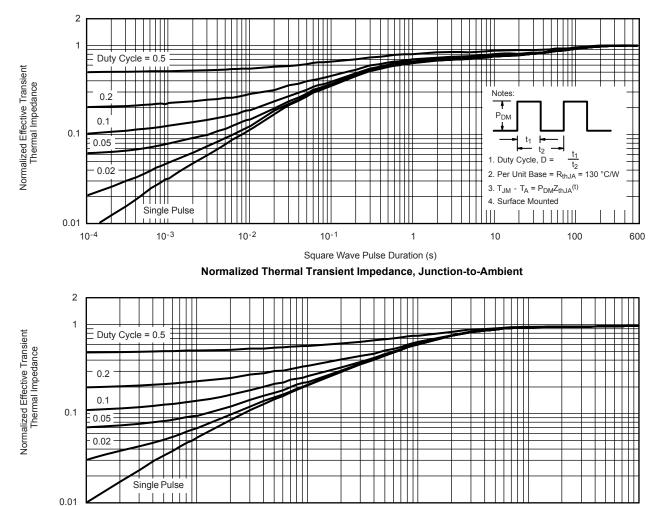
Time (s)

Single Pulse Power (Junction-to-Ambient)

10-4

10⁻³

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P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Foot

10-1

1

10-2

10



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